

**Amendments to the Claims**

Claims 1-23 - Cancelled

24. (Previously Presented) A Time Dependent Dielectric Breakdown (TDDB) test pattern circuit, comprising:

a plurality of unit test cells, each unit test cell includes a voltage force node (VFN) and a drain current measuring node (DCMN), such that all VFNs are commonly connected and all DCMNs are commonly connected;

wherein each unit test cell further includes:

a MOS capacitor with a first electrode connected to ground;

a MOS transistor with a source electrode connected to the first electrode of the MOS capacitor and a drain electrode connected to the DCMN; and

a fuse with a first end connected to the VFN and a second end connected to a second electrode of the MOS capacitor and the second end of the fuse also connected to a gate of the MOS transistor.

25. (Previously Presented) The test pattern circuit of claim 24, wherein the fuse is a metal line having a smaller width than a wiring line of the unit test cell.

26. (Previously Presented) The test pattern circuit of claim 24, wherein a type of the MOS capacitor is the same as a type of the MOS transistor.

27. (Previously Presented) The test pattern circuit of claim 26, wherein both the type of the MOS capacitor and the type of the MOS transistor is NMOS.

28. (Previously Presented) The test pattern circuit of claim 27, further comprising:

a substrate pad connecting the MOS capacitor with a bulk electrode of the MOS transistor;

a source pad commonly connecting the source electrodes of MOS transistors;

a VFN pad commonly connecting the VFNs of all unit test cells; and

a DCMN pad commonly connecting the DCMNs of all unit test cells.

29. (Previously Presented) The test pattern circuit of claim 24, wherein a type of the MOS capacitor is different from a type of the MOS transistor.

30. (Previously Presented) The test pattern circuit of claim 29, wherein the type of the MOS capacitor is NMOS and the type of the MOS transistor is PMOS.

31. (Previously Presented) The test pattern circuit of claim 30, wherein a source and drain are formed for each MOS capacitor and further comprising:

a substrate pad connecting the MOS capacitor with a bulk electrode of the MOS transistor;

a first source pad commonly connecting the source electrodes of all MOS transistors;

a second source pad commonly connecting the sources of all MOS capacitors;

a drain pad commonly connecting the drains of all MOS capacitors;

a VFN pad commonly connecting the VFNs of all unit test cells; and

a DCMN pad commonly connecting the DCMNs of all unit test cells.

32. (Previously Presented) The test pattern circuit of claim 24, wherein a gate oxide film of the MOS transistor is thicker than a dielectric of the MOS capacitor.

33. (Previously Presented) The test pattern circuit of claim 24, wherein the gate electrode of the MOS transistor is lightly doped such that a voltage applied to the gate electrode is less than the VFN voltage.

34. (Previously Presented) A Time Dependent Dielectric Breakdown (TDDB) test pattern circuit, comprising:

a plurality of unit test cells, each unit test cell includes a voltage force node (VFN) and a drain current measuring node (DCMN), such that all VFNs are commonly connected and all DCMNs are commonly connected;

a first voltage source supplying a stress voltage to the VFN of all unit test cells;

a second voltage source supplying voltage to the DCMN of all unit test cells; and

an ammeter connected between the DCMNs and the second voltage source.

Claims 35-36 - Cancelled